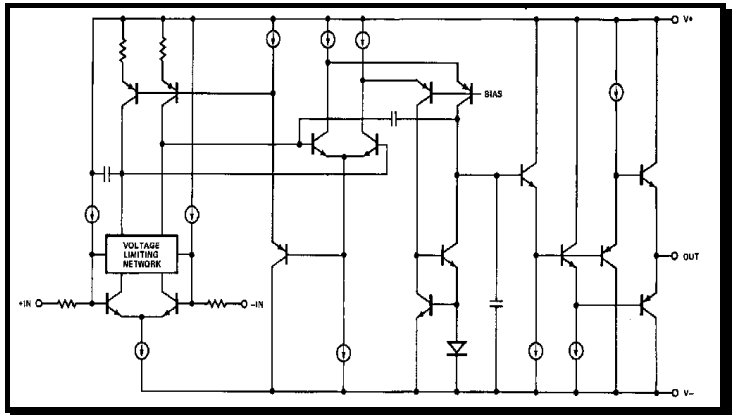
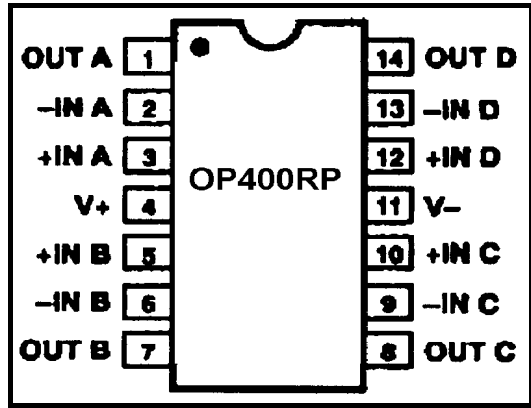


SEi - Radiation-Hardened OP400RP

Quad Low-Offset, Low-Power Operational Amplifier



Features:

- RAD-PAK[®] technology-hardened against natural space radiation
- Total dose hardness typical >100 krad (Si); dependent upon orbit
- Package:
 - 14 pin RAD-PAK[®] flat package
 - 28 pin RAD-PAK[®] quad flat package
- Low input offset voltage 150 μ V max
- Low offset voltage drift
 - +1.2 μ V/ $^{\circ}$ C max (over -55 $^{\circ}$ C to +125 $^{\circ}$ C)
- Low supply current (per amplifier) 725 μ A max
- High open-loop gain 5000V/mV min
- Input bias current 3nA Max
- Low noise voltage density 11nV per $\sqrt{\text{Hz}}$ at 1 kHz
- Stable with large capacitive loads 10nF typ

SEi's OP400RP (RP for RAD-PAK[®]) monolithic quad operational amplifier microcircuit features a 100 kilorad (Si) typical total dose tolerance; dependent upon orbit. Using SEi's radiation-hardened RAD-PAK[®] packaging technology, the OP400RP has an extremely low input offset voltage no less than 150 μ V with a drift of under 1.2 μ V/ $^{\circ}$ C, guaranteed over the full military temperature range. The OP400RP features low power consumption, drawing less than 725 μ A per amplifier. Capable of surviving space environments, the OP400RP is ideal for satellite, spacecraft, and space probe missions. The patented radiation-hardened RAD-PAK[®] technology incorporates radiation shielding in the microcircuit package. It eliminates box shielding while providing required lifetime in orbit. This product is available with packaging and screening up to Class S.



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OP400RP ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	MIN	MAX	UNIT
Supply Voltage	V_{CC}		+20	V
Differential Input Voltage			+30	V
Input Voltage				Supply Voltage
Output Short-Circuit Duration				Continuous
Storage Temperature Range	T_S	65	150	°C
Operating Temperature Range	T_A	55	125	°C

Note:

1. Absolute ratings apply to both DICE and packaged parts, unless otherwise noted.

OP400RP ELECTRICAL CHARACTERISTICS

($V_S = \pm 15V$, $T_A = +25^\circ C$, unless otherwise specified)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Offset Voltage	V_{OS}	---	---	40	150	μV
Long Term Input Voltage Stability	---	---	---	0.1	---	$\mu V/mo$
Input Offset Current	I_{OS}	$V_{CM} = 0V$	---	0.1	1.0	nA
Input Bias Current	I_B	$V_{CM} = 0V$	---	0.75	3.0	nA
Input Noise Voltage	$e_{n,p-p}$	0.1Hz to 10Hz	---	0.5	---	μV_{p-p}
Input Noise Voltage Density	e_n	$f_o = 10Hz$ 1/ $f_o = 1KHz$ 1/	---	22 11	36 18	$nV/\sqrt{Hz}$
Input Noise Current	$i_{n,p-p}$	0.1Hz to 10Hz	---	15	---	pA_{p-p}
Input Noise Current Density	i_n	$f_o = 10Hz$	---	0.6	---	$pA/\sqrt{Hz}$
Input Resistance Differential Mode	R_{IN}	---	---	10	---	$M\Omega$
Input Resistance Common Mode	R_{INCM}	---	---	200	---	$G\Omega$
Large Signal Voltage Gain	A_{VO}	$V_O = \pm 10V$ $R_L = 10k\Omega$ $R_L = 2k\Omega$	5000 2000	12000 3500	---	V/mV
Input Voltage Range	IVR	3/	± 12	± 13	---	V
Common Mode Rejection	CMR	$V_{CM} = \pm 12V$	120	140	---	dB
Power Supply Rejection Ratio	PSRR	$V_S = \pm 3V$ to $\pm 18V$	---	0.1	1.8	$\mu V/V$
Output Voltage Swing	V_O	$R_L = 10k\Omega$ $R_L = 2k\Omega$	± 12 ± 11	± 12.6 ± 12.2	---	V
Supply Current Per Amplifier	I_{SV}	No Load	---	600	725	μA
Slew Rate	SR	---	0.1	0.15	---	V/ μs
Gain Bandwidth Product	GBWP	$A_V = +1$	---	500	---	kHz
Channel Separation	CS	$V_O = 20V_{p-p}$ $f_o = 10Hz$ 2/	123	135	---	dB
Input Capacitance	C_{IN}	---	---	3.2	---	pF
Capacitive Load Stability		$A_V = +1$ No Oscillations	---	10	---	nF

Notes:

- 1/ Sample tested.
- 2/ Guaranteed but not 100% tested.
- 3/ Guaranteed by CMR test.



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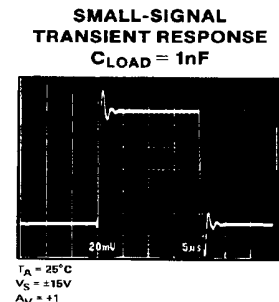
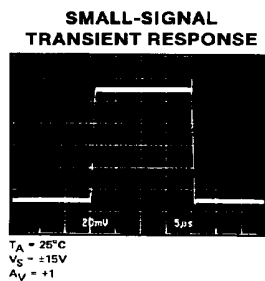
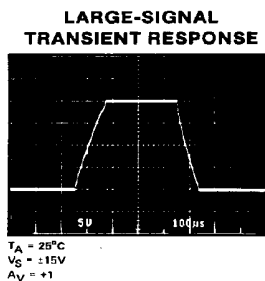
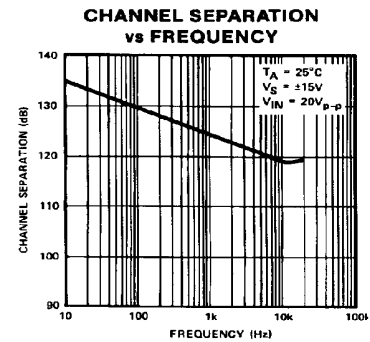
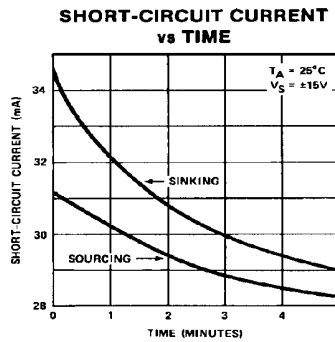
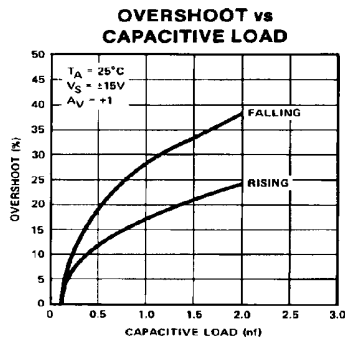
OP400RP ELECTRICAL CHARACTERISTICS
($V_S = \pm 15V$, $-55^\circ C \leq T_A \leq 125^\circ C$ unless otherwise specified.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Input Offset Voltage	V_{OS}	---	---	70	270	μV
Average Input Offset Voltage Drift	TCV_{OS}	---	---	0.3	1.2	$\mu V/^\circ C$
Input Offset Current	I_{OS}	$V_{CM} = 0V$	---	0.1	2.5	nA
Input Bias Current	I_B	$V_{CM} = 0V$	---	1.3	5.0	nA
Large Signal Voltage Gain	A_{VO}	$V_O = \pm 10V$ $R_L = 10k\Omega$ $R_L = 2k\Omega$	3000 1000	9000 2300	---	V/mV
Input Voltage Range	IVR	(Note 1)	± 12	± 12.5	---	V
Common Mode Rejection	CMR	$V_{CM} = \pm 12V$	115	130	---	dB
Power Supply Rejection Ratio	PSRR	$V_S = \pm 3V$ to $\pm 18V$	---	0.2	3.2	$\mu V/V$
Output Voltage Swing	V_O	$R_L = 10k\Omega$ $R_L = 2k\Omega$	± 12 ± 11	± 12.4 ± 12	---	V
Supply Current Per Amplifier	I_{SV}	No Load	---	600	775	μA
Capacitive Load Stability		$A_V = +1$ No Oscillations	---	8	---	nF

Notes:

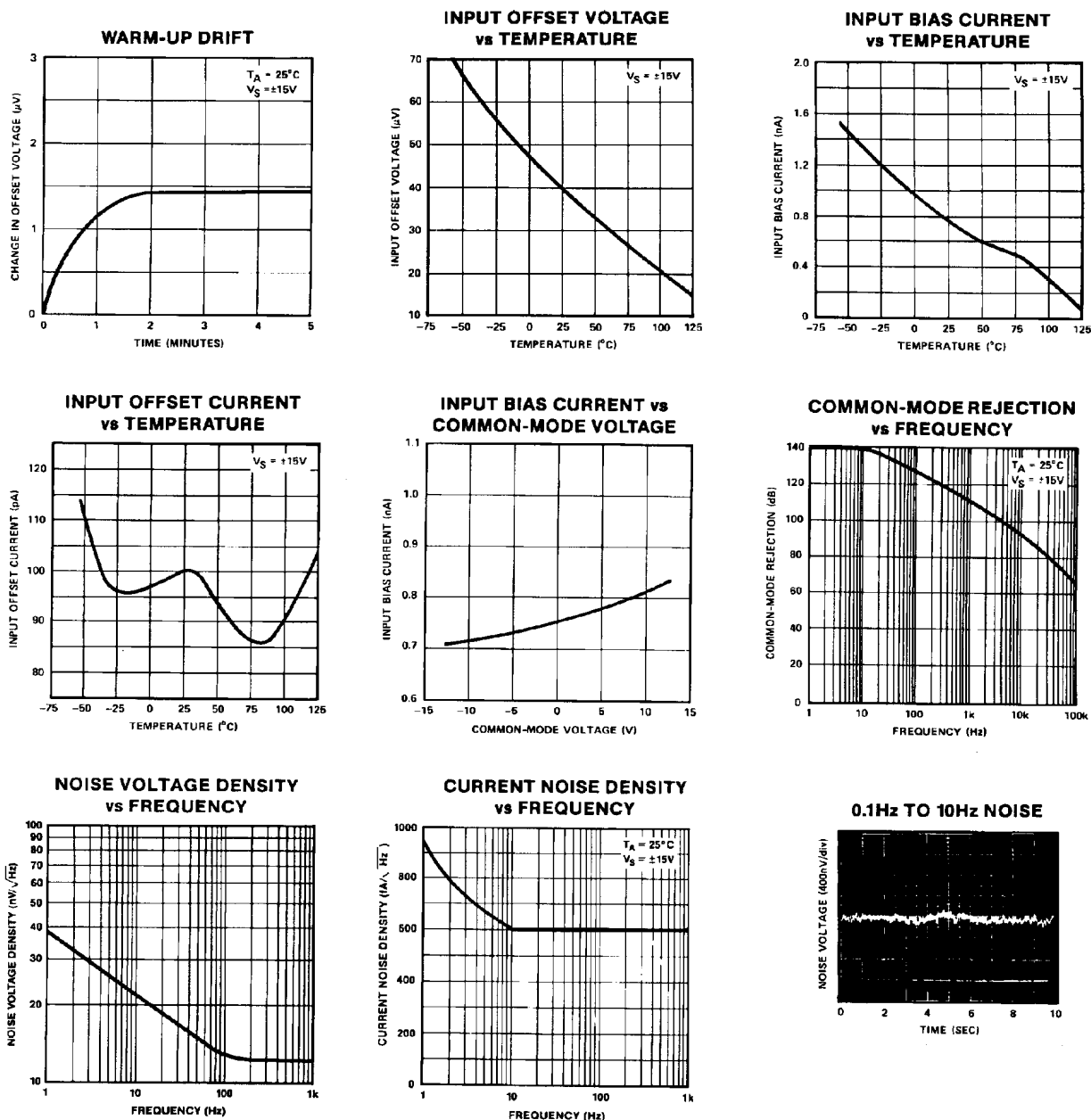
1. Guaranteed by design.

OP400RP TYPICAL PERFORMANCE CHARACTERISTICS



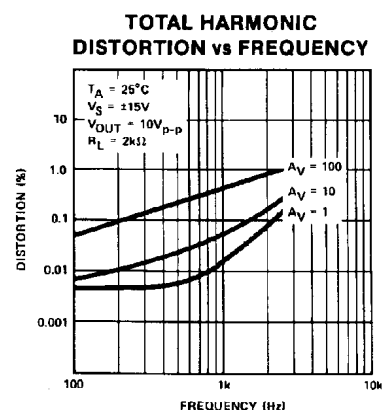
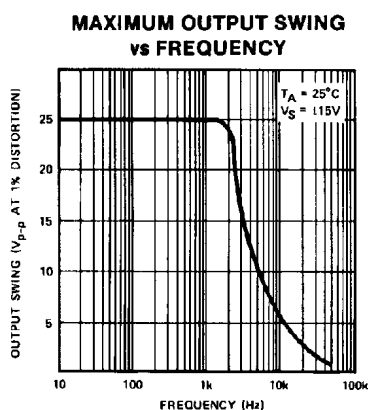
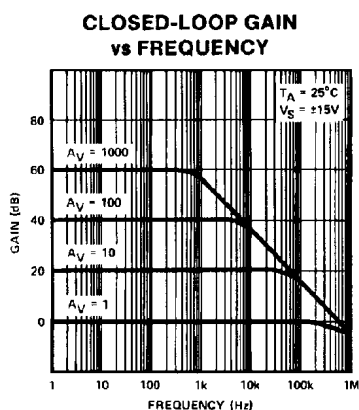
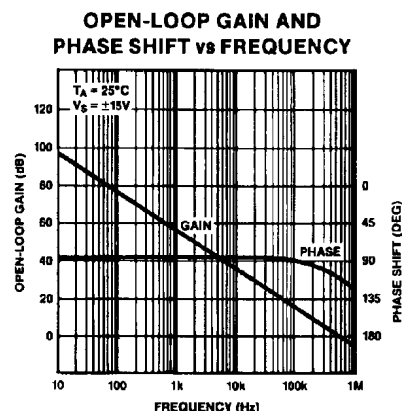
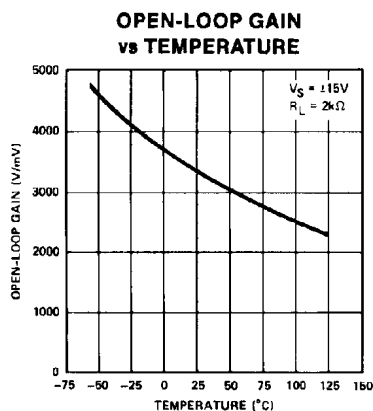
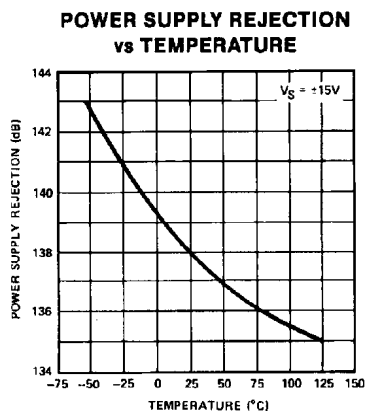
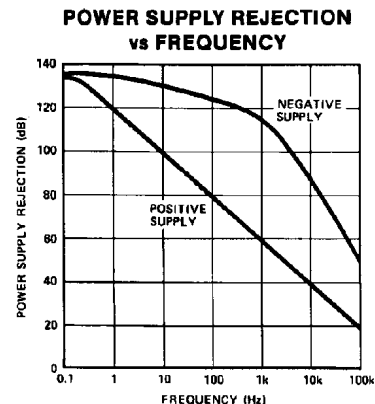
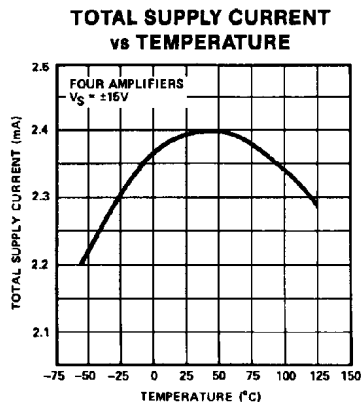
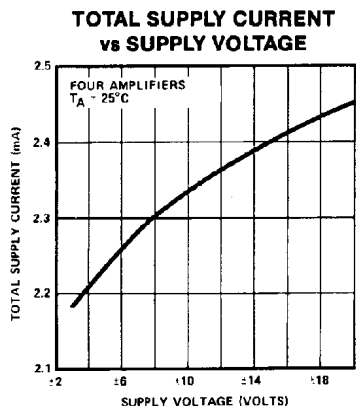
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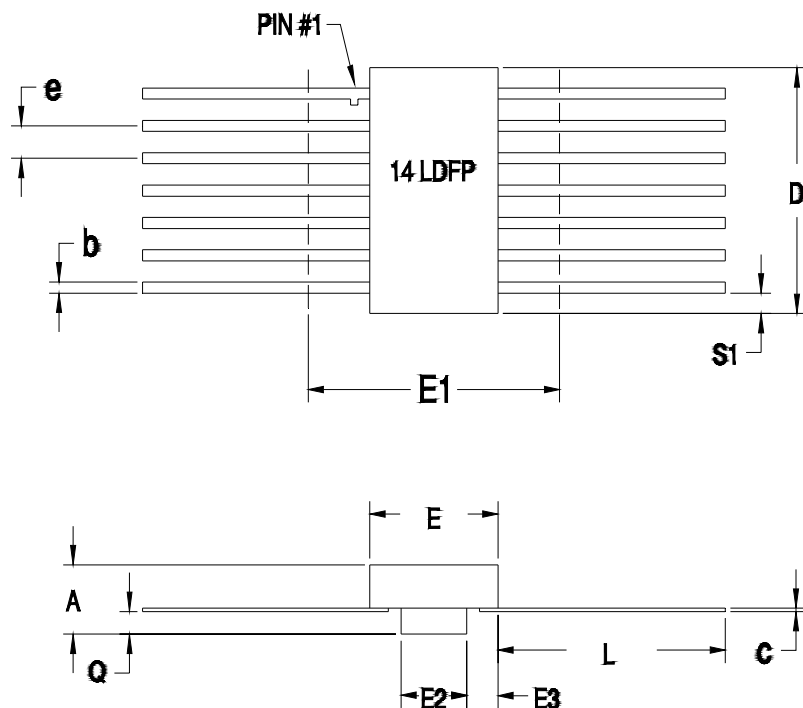
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14 PIN FLAT PACKAGE

SYMBOL	DIMENSION		
	MIN	NOM	MAX
A	0.155	0.170	0.185
b	0.015	0.017	0.022
c	0.004	0.005	0.009
D	--	0.380	0.390
E	0.250	0.255	0.260
E1	--	--	0.290
E2	0.125	0.131	--
E3	0.030	0.062	--
e	0.050 BSC		
L	0.279	0.325	0.370
Q	0.026	0.045	0.055
S1	0.005	--	--
N	14		

F14-04

Note: All dimensions in inches.

